

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An electro-optical device comprising ~~above~~ a substrate:

data lines extending in a first direction;

scanning lines extending in a second direction in such a manner that the

scanning lines and data lines cross each other;

pixel electrodes and thin-film transistors each placed in regions corresponding

to intersections of the scanning lines and data lines, the thin-film transistor disposed below
the data lines;

storage capacitors each disposed below the data lines and each electrically connected to the corresponding thin-film transistors and pixel electrodes;

a capacitor line shielding layer disposed above below the pixel electrodes and
disposed to cover the data lines are characterized by;

first junction electrodes, formed using the same film as that for forming the
data lines, for each electrically connecting the corresponding constant potential capacitor
electrodes, and the shielding layer,

first junction electrodes, formed using the same film as that for forming the
data lines, for each electrically connecting the corresponding pixel potential capacitor
electrodes of the storage capacitors and pixel electrodes; and

second junction electrodes, formed using the same film as that for forming the
data lines, for each electrically connecting the corresponding constant potential capacitor
electrodes and the capacitor line,

second junction electrodes, formed using the same film as that for forming the data lines, for each electrically connecting the corresponding pixel potential capacitor electrodes of the storage capacitors and pixel electrodes; and

wherein the data lines, first junction electrodes, and second junction electrodes each include a nitride film.

2. (Original) The electro-optical device according to Claim 1, wherein the data lines, first junction electrodes, and second junction electrodes each include the nitride film on a conductive layer.

3 (Original) The electro-optical device according to Claim 2, wherein the data lines, first junction electrodes, and second junction electrodes have laminated layer structure including an aluminum film, titanium nitride film, and silicon nitride film.

4. (Original) The electro-optical device according to Claim 1 further comprising third junction electrodes formed using the same film as that for forming the capacitor line, wherein the first junction electrodes are each electrically connected to the corresponding pixel electrodes with the corresponding third junction electrodes.

5. (Original) The electro-optical device according to Claim 4, wherein the capacitor line and third junction electrodes each include a conductive layer and a nitride film disposed thereon.

6. (Original) The electro-optical device according to Claim 5, wherein the capacitor line and third junction electrodes have laminated layer structure including an aluminum film, titanium nitride film, and silicon nitride film.

7. (Currently Amended) The electro-optical device according to Claim 1-Claim 4 further comprising fourth junction electrodes formed on an insulating layer on which the thin-film transistors are formed, wherein the pixel potential capacitor electrodes are each

electrically connected to the corresponding first junction electrodes with the corresponding fourth junction electrodes.

8. (Original) The electro-optical device according to Claim 7, wherein the fourth junction electrodes are formed using the same film for forming gate electrodes of the thin-film transistors.

9. (Original) The electro-optical device according to Claim 1, wherein the scanning lines are placed below the thin-film transistors and each electrically connected to the corresponding gate electrodes with contact holes, the gate electrodes being each disposed on corresponding semiconductor layers each included in the corresponding thin-film transistors.

10. (Original) The electro-optical device according to Claim 1, wherein the storage capacitors each include corresponding dielectric layers each disposed between the corresponding pixel potential capacitor electrodes and constant potential capacitor electrodes, the dielectric layers include a plurality of sub-layers containing different materials, and one of the sub-layers contains a material having a dielectric constant larger than those of the materials of the other layers.

11. (Original) The electro-optical device according to Claim 10, wherein the dielectric layers each include corresponding silicon dioxide sub-layers and silicon nitride sub-layers.

12. (Original) The electro-optical device according to Claim 1, wherein the capacitor line is made of a light-shielding film and extend along the corresponding data lines and have a width larger than that of the data lines.

13. (Original) The electro-optical device according to Claim 1 further comprising a first insulating layer disposed under the pixel electrodes as the base and a second insulating layer disposed under the capacitor line as the base, wherein at least the surface of the first insulating layer is planarized.

14. (Original) An electronic apparatus including an electro-optical device, the electro-optical device comprising, above a substrate:

data lines extending in a first direction; scanning lines extending in a second direction in such a manner that the scanning lines and data lines cross each other; pixel electrodes and thin-film transistors each placed in corresponding regions corresponding to intersections of the scanning lines and data lines; the storage capacitors disposed below the data lines and each electrically connected to the corresponding thin-film transistors and pixel electrodes; capacitor line disposed above the data lines; first junction electrodes, formed using the same film as that for forming the data lines, for each electrically connecting the corresponding pixel potential capacitor electrodes and pixel electrodes; and second junction electrodes, formed using the same film as that for forming the data lines, for each electrically connecting the corresponding constant potential capacitor electrodes and the capacitor line,

wherein the data lines, first junction electrodes, and second junction electrodes each include a nitride film.

15. (Original) A process for manufacturing an electro-optical device comprising the steps of forming above a substrate:

thin-film transistors;

a first interlayer insulating layer on gate electrodes of the thin-film transistors;

storage capacitors each by forming on the first interlayer insulating layer, the storage capacitors being each equipped with a pixel potential capacitor electrode, dielectric layer, and constant potential capacitor electrode disposed in this order from the bottom;

a second interlayer insulating layer on the storage capacitors;

data lines, first junction electrodes, and second junction electrodes on the second interlayer insulating layer using a conductive material containing a nitride film, the data lines being each electrically connected to the corresponding semiconductor layers of the

thin-film transistors, the first junction electrodes being each electrically connected to the corresponding pixel potential capacitor electrodes, and the second junction electrodes being each electrically connected to the corresponding constant potential capacitor electrodes;

 a third interlayer insulating layer on the data lines, first junction electrodes, and second junction electrodes;

 third junction electrodes and a capacitor line on the third interlayer insulating layer, the third junction electrodes being each electrically connected to the corresponding first junction electrodes, and the capacitor line being electrically connected to the corresponding second junction electrodes;

 a fourth interlayer insulating layer on the third junction electrodes and capacitor line; and

 pixel electrodes, each electrically connected to the corresponding third junction electrodes, on the fourth interlayer insulating layer.

16. (Original) The process according to Claim 15, wherein the step of forming the storage capacitors includes a sub-step of forming a first precursor film for forming the pixel potential capacitor electrodes; a sub-step of forming a second precursor film for forming the dielectric layers on the first precursor film; a sub-step of forming a third precursor film for forming the constant potential capacitor electrodes on the second precursor film; and a sub-step of etching the first, second, and third precursor films in one step to form the pixel potential capacitor electrodes, dielectric layers, and constant potential capacitor electrodes.

17. (Original) The process according to Claim 15, wherein the step of forming the storage capacitors includes a sub-step of forming a first precursor film for forming the pixel potential capacitor electrodes; a sub-step of etching the first precursor film to form the pixel potential capacitor electrodes; a sub-step of forming a second precursor film for forming the dielectric layers on the first precursor film; a sub-step of forming a third precursor film for

forming the constant potential capacitor electrodes on the second precursor film; and a sub-step of etching the third precursor film to form the dielectric layers and constant potential capacitor electrodes, wherein the constant potential capacitor electrodes have an area larger than that of the dielectric layers and pixel potential capacitor electrodes.

18. (New) An electro-optical device, comprising:

a substrate;

data lines extending in a first direction;

scanning lines extending in a second direction in such a manner that the scanning lines and data lines cross each other;

pixel electrodes and thin-film transistors each placed in regions corresponding to intersections of the scanning lines and data lines, the thin-film transistor disposed below the data lines;

storage capacitors each disposed below the data lines and each electrically connected to the corresponding thin-film transistors and pixel electrodes;

a shielding layer disposed below the pixel electrodes and disposed to cover the data lines;

first junction electrodes, formed using the same film as that for forming the data lines, for each electrically connecting the corresponding constant potential capacitor electrodes and the shielding layer,

second junction electrodes, formed using the same film as that for forming the data lines, for each electrically connecting the corresponding pixel potential capacitor electrodes of the storage capacitors and pixel electrodes; and

wherein the data lines, first junction electrodes, and second junction electrodes each include a nitride film.